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- (54) Title: SILICON IMPLANTATION IN SUBSTRATES AND PROVISION OF SILICON PRECURSOR COMPOSITIONS THEREFOR

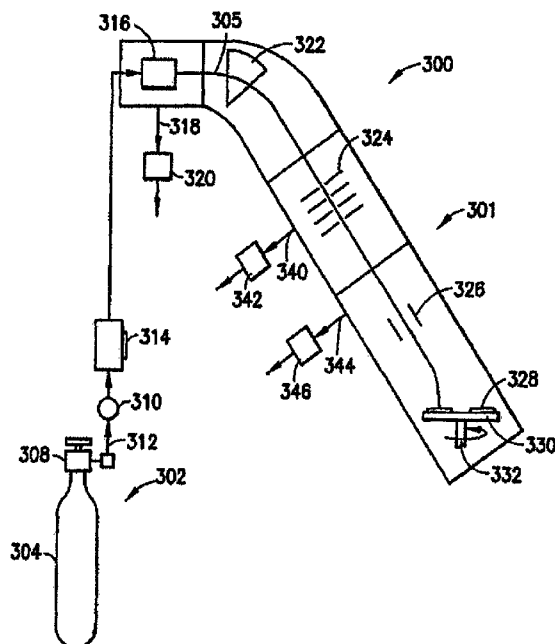


FIG. 1

- (57) Abstract: Compositions, systems, and methods are described for implanting silicon and/or silicon ions in a substrate, involving generation of silicon and/or silicon ions from corresponding silicon precursor compositions, and implantation of the silicon and/or silicon ions in the substrate.



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